

# ZXTP23015CFH 15V, SOT23, PNP medium power transistor

## Summary

 $V_{(BR)CES} > -15V, V_{(BR)CEO} > -15V$ 

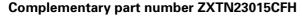
 $V_{(BR)ECO} > -6V$ 

 $I_{C(CONT)} = -6A$ 

 $R_{CE(SAT)} = 20m\Omega \text{ typical}$ 

 $V_{CE(SAT)} < -36mV @ -1A$ 

 $P_D = 1.25W$ 



## **Description**

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

## **Feature**

- · Higher power dissipation SOT23 package
- · High peak current
- · Low saturation voltage
- · 15V forward blocking voltage
- · 6V reverse blocking voltage

## **Applications**

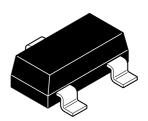
- · High side disconnect switches
- · DC DC converters
- MOSFET and IGBT gate driving
- · Motor drive
- · Relay, lamp, and solenoid drive

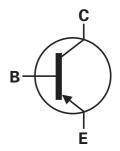
### **Ordering information**

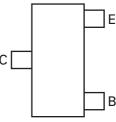
Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP23015CFHTA	7	8mm	3000

## **Device marking**

317







Pinout - top view

## **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-15	V
Collector-emitter voltage	V <sub>(BR)CES</sub>	-15	V
Collector-emitter voltage	V <sub>CEO</sub>	-15	V
Emitter-base voltage	V <sub>EBO</sub>	-7.0	V
Emitter-collector voltage	V <sub>ECO</sub>	-6.0	V
Peak pulse current	I <sub>CM</sub>	-10	А
Continuous collector current (c)	I <sub>C</sub>	-5	А
Continuous collector current (d)	I <sub>C</sub>	-6	А
Base current	I <sub>B</sub>	-1.2	Α
Power dissipation @ T <sub>A</sub> =25°C <sup>(a)</sup> Linear derating factor <sup>(a)</sup>	P <sub>D</sub>	0.73 5.84	W mW/°C
Power dissipation @ T <sub>A</sub> =25°C <sup>(b)</sup> Linear derating factor <sup>(b)</sup>	P <sub>D</sub>	1.05 8.4	W mW/°C
Power dissipation @ T <sub>A</sub> =25°C <sup>(c)</sup> Linear derating factor <sup>(c)</sup>	P <sub>D</sub>	1.25 9.6	W mW/°C
Power dissipation @ T <sub>A</sub> =25°C <sup>(d)</sup> Linear derating factor <sup>(d)</sup>	P <sub>D</sub>	1.81 14.5	W mW/°C
Operating and storage temperature	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

## Thermal resistance

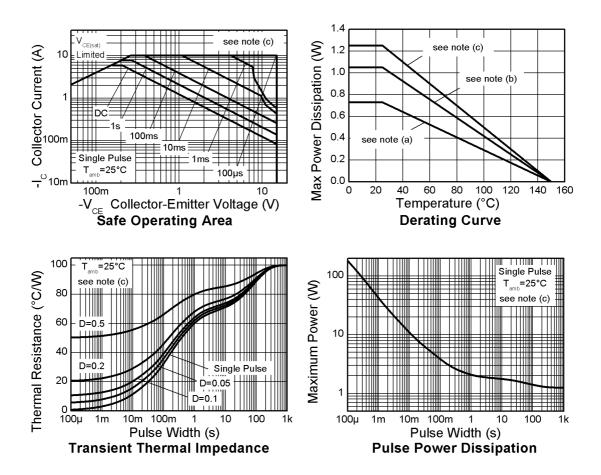
Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R\Theta_{JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R\Theta_{JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R\Theta_{JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R\Theta_{JA}$	69	°C/W

## NOTES:

<sup>(</sup>a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (d) As (c) above measured at t<5secs.

## **Characteristics**



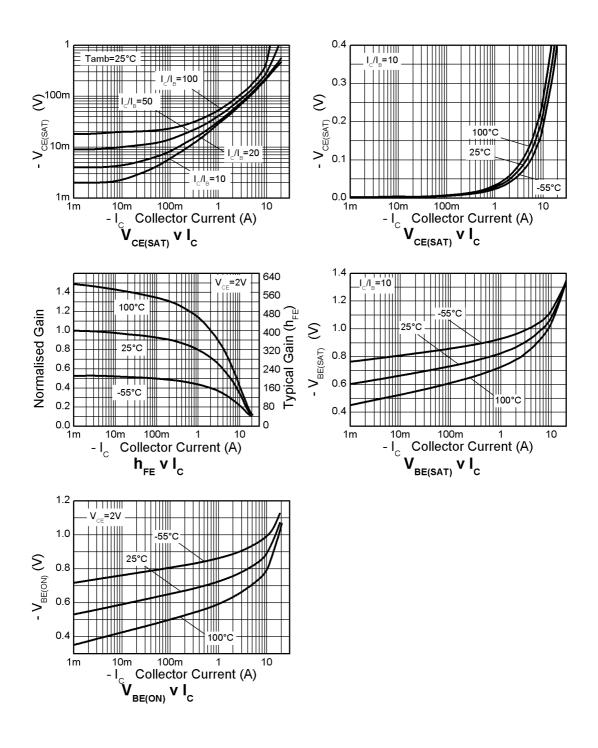
# ELECTRICAL CHARACTERISTICS (at $T_{AMB} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	-15	-40		V	I <sub>C</sub> =-100μA
Collector-emitter breakdown voltage	V <sub>(BR)CES</sub>	-15	-40		V	I <sub>C</sub> =-100μA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	-15	-25		V	I <sub>C</sub> =-10mA <sup>(*)</sup>
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	-7.0	-8.2		V	I <sub>E</sub> =-100μA
Emitter-collector breakdown voltage	V <sub>(BR)ECO</sub>	-6.0	-8.5		V	l <sub>E</sub> =-100μA
Collector-emitter cut-off current	I <sub>CES</sub>			-20	nA	V <sub>CE</sub> =-12V
Collector-base cut-off current	I <sub>CBO</sub>			-20	nA	V <sub>CB</sub> =-12V
Emitter-base cut-off current	I <sub>EBO</sub>			-10	nA	V <sub>EB</sub> =-6V
Static forward current transfer ratio	H <sub>FE</sub>	200	380			I <sub>C</sub> =-10mA, V <sub>CE</sub> =-2V <sup>(*)</sup>
ratio		200	350	560		I <sub>C</sub> =-500mA, V <sub>CE</sub> =-2V
		140	220			Ic=-6A, V <sub>CE</sub> =-2V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-6	-10	mV	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA <sup>(*)</sup>
voltage			-27	-36	mV	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA <sup>(*)</sup>
			-90	-120	mV	I <sub>C</sub> =-3A, I <sub>B</sub> =-60mA <sup>(*)</sup>
			-140	-190	mV	I <sub>C</sub> =-6A, I <sub>B</sub> =-240mA <sup>(*)</sup>
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-0.83	-0.93	V	I <sub>C</sub> =-3A, I <sub>B</sub> =-60mA <sup>(*)</sup>
			-0.93	-1.03	V	I <sub>C</sub> =-6A, I <sub>B</sub> =-240mA <sup>(*)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-0.83	-0.93	V	I <sub>C</sub> =-6A, V <sub>CE</sub> =-2V <sup>(*)</sup>
Transition frequency	f <sub>T</sub>		270		MHz	Ic=-500mA, V <sub>CE</sub> =-2V, f=50MHz
Output capacitance	C <sub>obo</sub>		78.4		pF	V <sub>CB</sub> =-10V, f=1MHz
Delay time	t (d)		16		ns	V <sub>CC</sub> =-5V, I <sub>C</sub> =-3A,
Rise time	t (r)		13		ns	I <sub>B1</sub> =I <sub>B2</sub> =-150mA
Storage time	t <sub>(stg)</sub>		123		ns	
Fall time	t <sub>(f)</sub>		9		ns	

#### NOTES

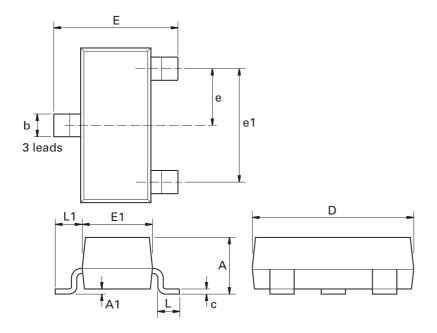
(\*) Measured under pulsed conditions. Pulse width = 300  $\mu S$  . Duty cycle  ${\le}2\%$  .

## **Typical characteristics**



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## Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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